

SMALL SIGNAL NPN TRANSISTORS

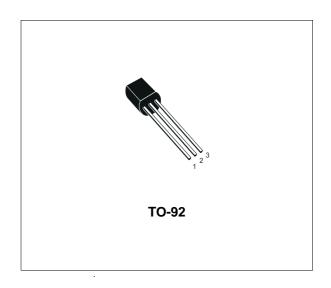
| Туре | Marking |
|--------|---------|
| BC547B | BC547B |
| BC547C | BC547C |

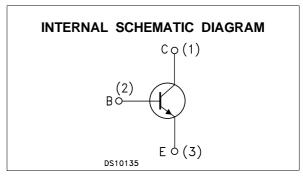
- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- BC547B THE PNP COMPLEMENTARY TYPE IS BC557B

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APPLICATIONS

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit | | |
|------------------|--|--------------------------------------|------|--|--|
| V_{CBO} | Collector-Base Voltage (I _E = 0) | Base Voltage (I _E = 0) 50 | | | |
| V_{CEO} | Collector-Emitter Voltage (I _B = 0) | 45 | V | | |
| V _В | Emitter-Base Voltage (Ic = 0) | 6 | V | | |
| Ic | Collector Current | 100 | mA | | |
| I _{CM} | Collector Peak Current | 200 | mA | | |
| P _{tot} | Total Dissipation at T _C = 25 °C | 500 | mW | | |
| T _{stg} | Storage Temperature | -65 to 150 | °C | | |
| Tj | Max. Operating Junction Temperature | 150 | °C | | |

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THERMAL DATA

| R _{thj-amb} • | Thermal Resistance Junction-Ambient | Max | 250 | °C/W |
|-------------------------|-------------------------------------|-----|------|------|
| R _{thj-Case} • | Thermal Resistance Junction-Case | Max | 83.3 | °C/W |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

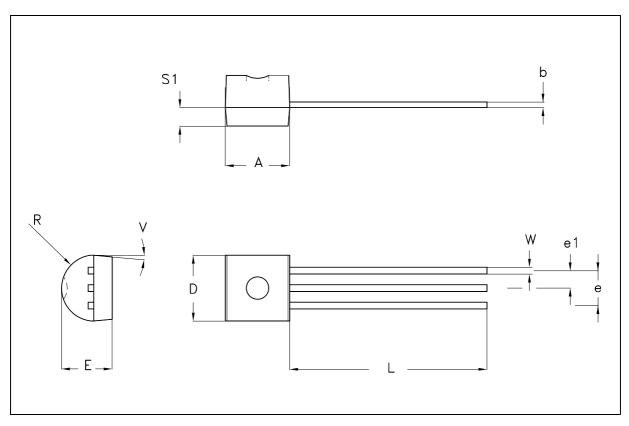
| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|------------------------|--|---|------------|-------------|-------------|----------|
| Ісво | Collector Cut-off Current (I _E = 0) | V _{CB} = 30 V V _{CB} = 30 V T _C = 150 °C | | | 15 5 | nA μA |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | 100 | nA |
| V _{(BR)CEO*} | Collector-Emitter Breakdown Voltage (I _B = 0) | I _C = 10 mA | 45 | | | V |
| V _{CE(sat)*} | Collector-Emitter Saturation Voltage | $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | | 0.09 0.2 | 0.25 0.6 | V V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | | 0.7 0.9 | | V V |
| V _{BE(on)} * | Base-Emitter On Voltage | $\begin{tabular}{lc} I_C = 2 & mA & V_{CE} = 5 & V \\ I_C = 10 & mA & V_{CE} = 5 & V \\ \end{tabular}$ | 0.58 | 0.66 | 0.7 0.77 | V V |
| h _{FE} | DC Current Gain | I _C = 2 mA | 200 420 | | 450 800 | |
| f _T | Transition Frequency | $I_C = 10 \text{ mA } V_{CE} = 5 \text{ V } f = 100 \text{MHz}$ | 100 | | | MHz |
| Ссво | Collector-Base Capacitance | IE = 0 VCB = 10 V f = 1 MHz | | 1.5 | | pF |
| C _{EBO} | Emitter-Base Capacitance | I _C = 0 V _{EB} = 0.5 V f = 1 MHz | | 11 | | pF |
| NF | Noise Figure | $V_{CE} = 5 \text{ V}$ $I_{C} = 200 \mu\text{A}$ $f = 1 \text{KHz}$ $\Delta f = 200 \text{ Hz}$ $R_{G} = 2 K\Omega$ | | 2 | 10 | dB |

^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %

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TO-92 MECHANICAL DATA

| DIM. | mm | | inch | | | |
|------|----------|------|----------|----------|------|----------|
| 2 | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| А | 4.32 | | 4.95 | 0.170 | | 0.195 |
| b | 0.36 | | 0.51 | 0.014 | | 0.020 |
| D | 4.45 | | 4.95 | 0.175 | | 0.194 |
| E | 3.30 | | 3.94 | 0.130 | | 0.155 |
| е | 2.41 | | 2.67 | 0.095 | | 0.105 |
| e1 | 1.14 | | 1.40 | 0.045 | | 0.055 |
| L | 12.70 | | 15.49 | 0.500 | | 0.609 |
| R | 2.16 | | 2.41 | 0.085 | | 0.094 |
| S1 | 1.14 | | 1.52 | 0.045 | | 0.059 |
| W | 0.41 | | 0.56 | 0.016 | | 0.022 |
| V | 4 degree | | 6 degree | 4 degree | | 6 degree |



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